

FRD MODULE 100A/1200V/trr:250nsec

PD100F12

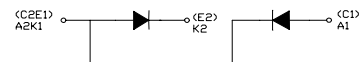
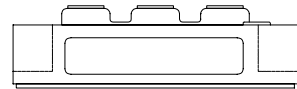
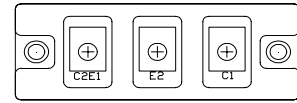
OUTLINE DRAWING

FEATURES

- * Isolated Base
- * Dual Diode Doubler Circuit
- * Ultra Fast Recovery
- * High Surge Capability
- * UL Recognized, File No. E187184

TYPICAL APPLICATIONS

- * High Frequency Rectification



Maximum Ratings

Approx Net Weight:210g

Voltage Rating	Symbol	PD100F12		Unit
Repetitive Peak Reverse Voltage per Arm	V_{RRM}	1200		V
Electrical Rating		Condition	Rating	
Average Rectified Output Current	I_o	50Hz Half Sine Wave condition per Arm $T_c=60^{\circ}C$	100	A
RMS Forward Current	$I_{F(RMS)}$	per Arm	157	A
Surge Forward Current	I_{FSM}	50 Hz Half Sine Wave, 1 cycle Non-repetitive per Arm	1000	A
I Squared t	I^2t	2 msec to 10 msec per Arm	5000	A ² s
Operating Junction Temperature Range	T_{jw}		-40 to +150	°C
Storage Temperature Range	T_{stg}		-40 to +125	°C
Isolation Voltage	Viso	Base Plate to Terminal, AC1min	2500	V
Mounting torque	Ftor	Case mounting(recommended)	2.8	N•m
		Terminal Screw(recommended)	2.8	

Electrical • Thermal Characteristics

Characteristics	Symbol	Test Conditions	Max.	Unit
Peak Forward Voltage	V_{FM}	$I_{FM}= 100A$, $T_j=25^{\circ}C$, per Arm	2.60	V
Peak Reverse Current	I_{RM}	$V_{RM}= V_{RRM}$, $T_j= 150^{\circ}C$, per Arm	20	mA
Reverse Recovery Time	trr	$I_{FM}= 10A$, $-di/dt= 50 A/\mu s$, $T_a= 25^{\circ}C$ Per Arm	250	ns
Thermal Resistance	$R_{th(j-c)}$	Junction to Case per Arm	0.28	°C/W
	$R_{th(c-f)}$	Base Plate to Heat Sink with Thermal Compound	0.1	
Internal Lead Inductance	L_s	Anode Terminal to Cathode Terminal Per Element	30	nH

PD100F12 OUTLINE DRAWING (Dimensions in mm)

